

N-channel TrenchMOS intermediate level FET Rev. 1 — 18 August 2010

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A};$ T _j = 25 °C; see <u>Figure 11;</u> see <u>Figure 12</u>		-	2	2.3	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 120 \text{ A}; \text{V}_{\text{sup}} \leq 40 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	1.02	J
Dynamic of	characteristics					
Q _{GD}	gate-drain charge	$\begin{split} I_D &= 25 \text{ A}; V_{DS} = 32 \text{ V}; \\ V_{GS} &= 10 \text{V}; \text{ see } \underline{\text{Figure 13}}; \\ \text{see } \underline{\text{Figure 14}} \end{split}$	-	72	-	nC

[1] Continuous current is limited by package.

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	Drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT226 (I2PAK)	

Ordering information 3.

Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
BUK6E2R3-40C	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

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Limiting values 4.

Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[3]	-	120	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[3]	-	120	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 3		-	1006	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	120	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	1006	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 120 \; A; \; V_sup \leq 40 \; V; \; R_GS = 50 \; \Omega; \\ V_GS = 10 \; V; \; T_j(init) = 25 \; ^\circ C; \; unclamped \end{array}$		-	1.02	J
E _{DS(AL)R}	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs

[2] Accumulated pulse duration not to exceed 5mins.

Continuous current is limited by package. [3]

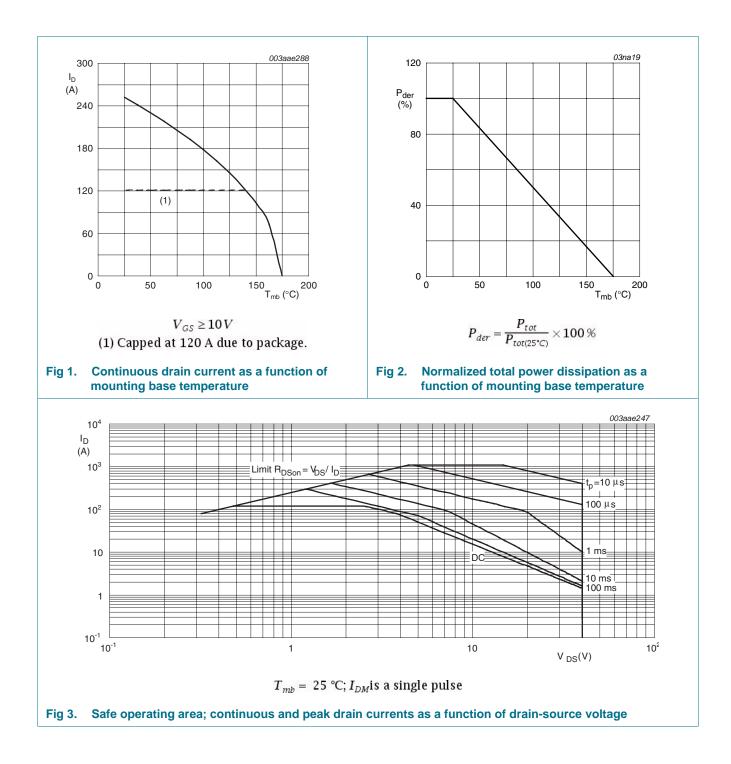
Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [4]

Repetitive avalanche rating limited by an average junction temperature of 170 °C. [5]

Refer to application note AN10273 for further information. [6]

BUK6E2R3-40C

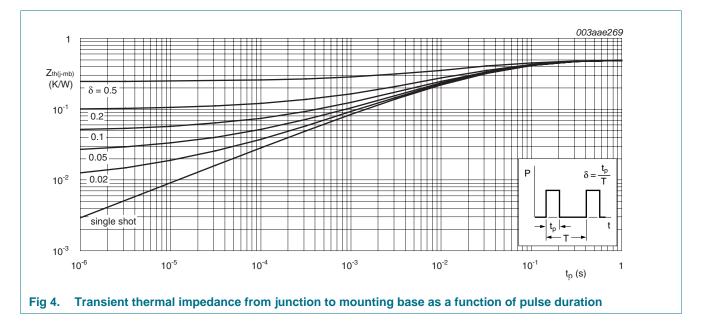
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <mark>Figure 4</mark>	-	-	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I _D = 2.5 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
DSS	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
GSS	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	2	2.3	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	2.5	3.1	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	2.8	3.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u>	-	-	5	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	260	-	nC	
		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	147	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	38	-	nC
Q _{GD}	gate-drain charge	see Figure 13; see Figure 14	-	72	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; \text{f} = 1 \text{MHz};$	-	11.3	15.1	nF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{1000}$	-	1447	1750	pF
C _{rss}	reverse transfer capacitance		-	1014	1390	pF
d(on)	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 $\Omega; ~V_{GS}$ = 10 V;	-	60	-	ns
r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	140	-	ns
d(off)	turn-off delay time		-	234	-	ns
f	fall time		-	416	-	ns
-D	internal drain inductance	from drain lead 6 mm from package to centre of die; T _j = 25 °C	-	4.5	-	nH
-S	internal source inductance	from source lead to source bond pad; $T_i = 25 ^{\circ}\text{C}$	-	7.5	-	nH

Symbol

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Max

Тур

Unit

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Min

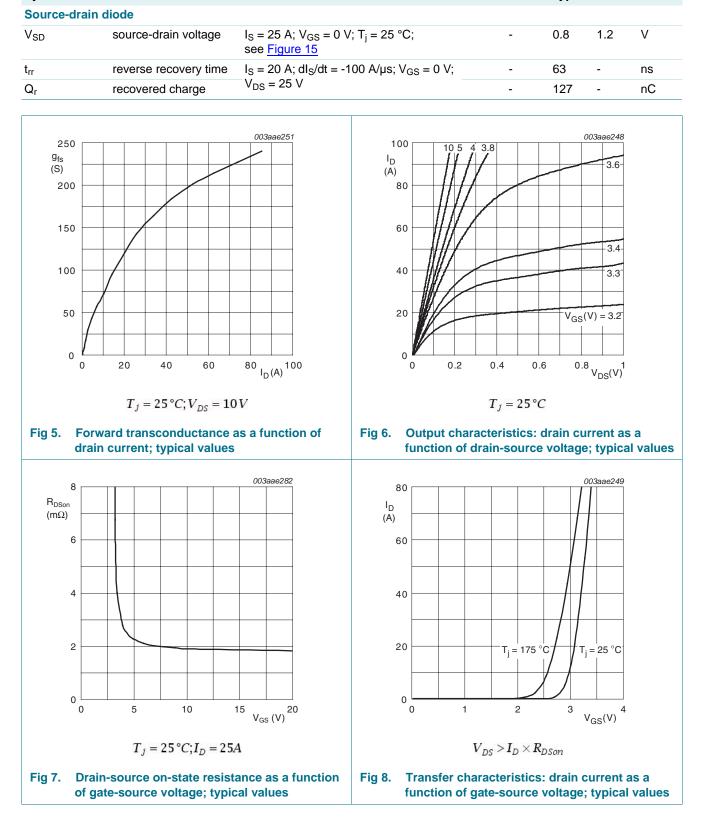


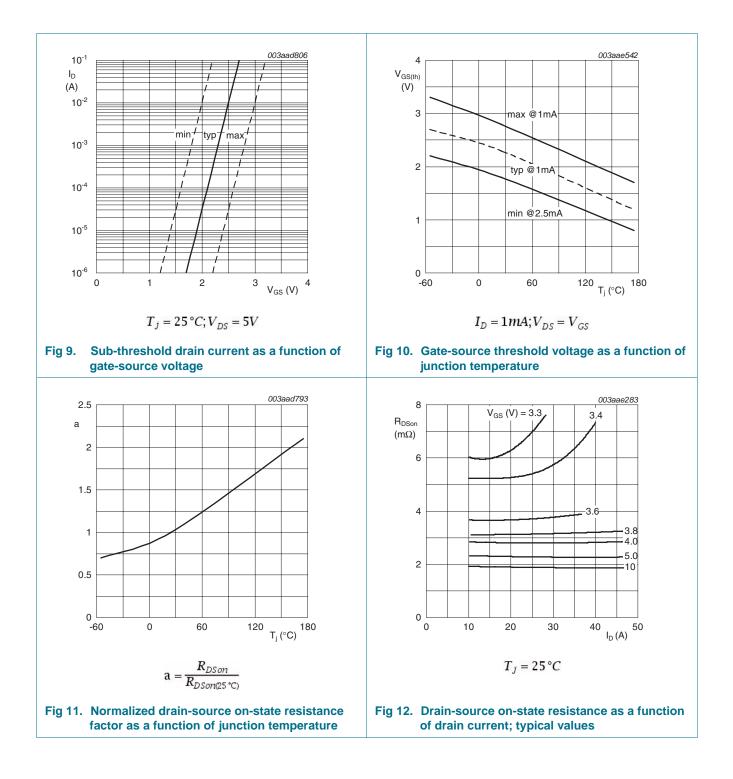
Table 6. Characteristics ...continued

Parameter

Conditions

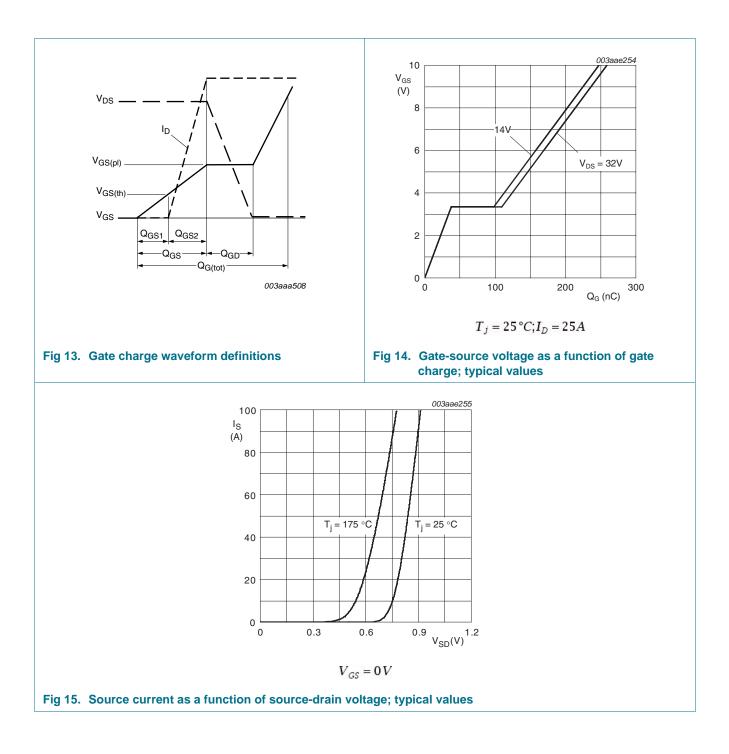
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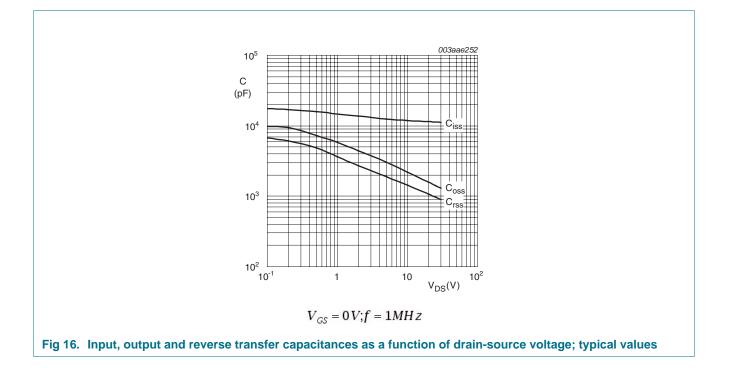
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7. Package outline

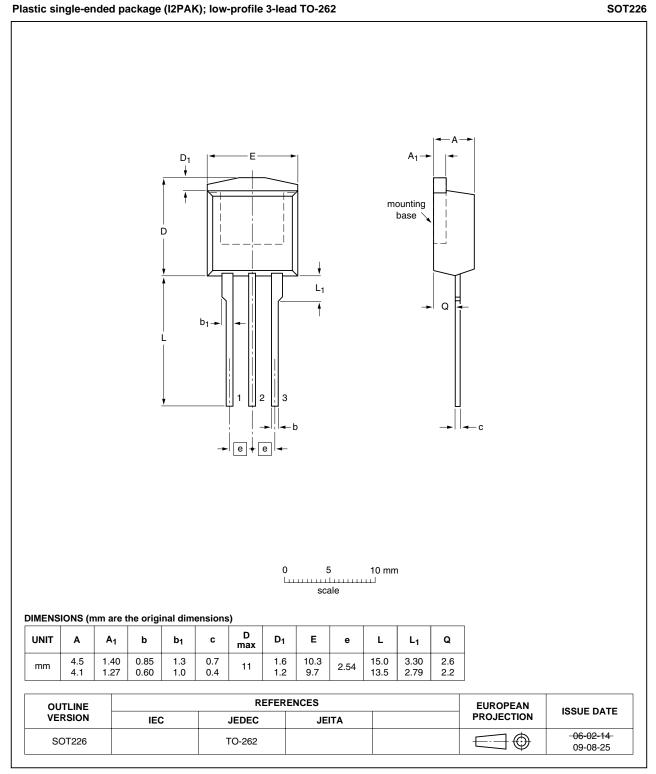


Fig 17. Package outline SOT226 (I2PAK)

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8. Revision history

Table 7. Revision h	7. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BUK6E2R3-40C v.1	20100818	Product data sheet	-	-			

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9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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